

isc Silicon NPN Power Transistor

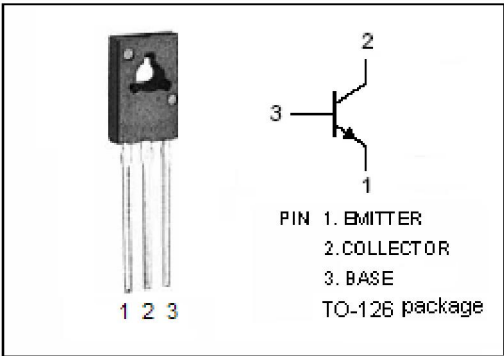
2SC3423

DESCRIPTION

- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 150V$ (Min)
- Complement to Type 2SA1360

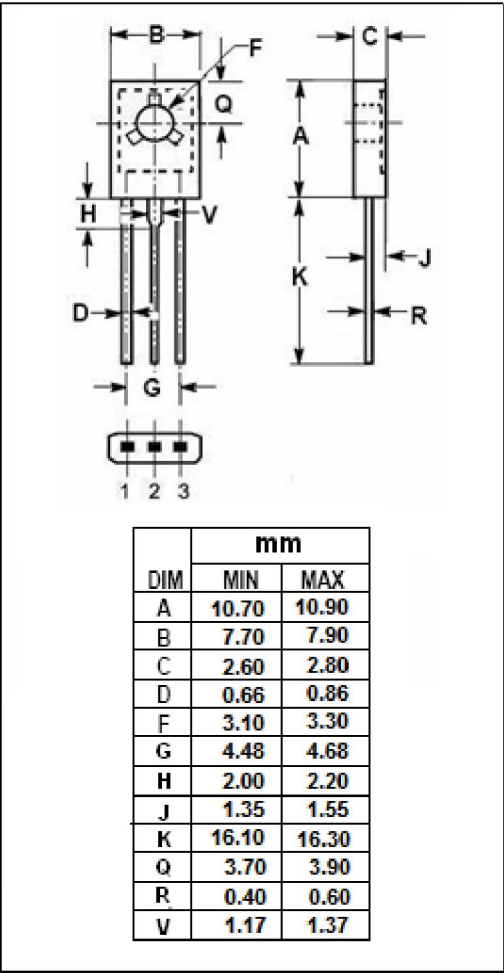
APPLICATIONS

- Designed for audio frequency amplifier applications.



ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	150	V
V_{CEO}	Collector-Emitter Voltage	150	V
V_{EBO}	Emitter-Base Voltage	5.0	V
I_C	Collector Current-Continuous	50	mA
I_B	Base Current-Continuous	5	mA
P_C	Collector Power Dissipation @ $T_a=25^{\circ}C$	1.2	W
	Total Power Dissipation @ $T_C=25^{\circ}C$	5	
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$



isc Silicon NPN Power Transistor**2SC3423****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 1mA; I _B = 0	150			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 10mA; I _B = 1mA			1.0	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = 10mA; V _{CE} = 5V			0.8	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 150V; I _E = 0			0.1	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0			0.1	μ A
h _{FE}	DC Current Gain	I _C = 10mA; V _{CE} = 5V	80		240	
f _T	Current-Gain—Bandwidth Product	I _C = 10mA; V _{CE} = 10V		200		MHz
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = 10V; f= 1.0MHz		1.8		pF

◆ h_{FE} Classifications

O	Y
80-160	120-240